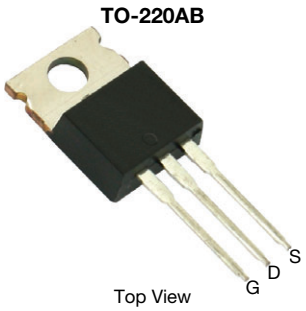
P-Channel 80 V (D-S) MOSFET



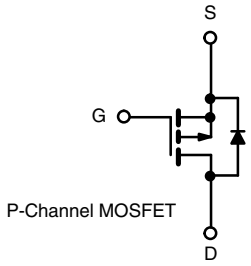
FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- Maximum 175 °C junction temperature
- Low $R_{DS(on)}$ minimizes power loss from conduction
- Compatible with logic-level gate driving
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Battery protection
- Motor drive control
- Load switch



PRODUCT SUMMARY	
V_{DS} (V)	-80
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.0058
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V	0.0081
Q_g typ. (nC)	145
I_D (A)	-150
Configuration	Single

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free and halogen-free	SUP60061EL-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-80	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current [d] (T_J = 175 °C)	T_C = 25 °C	I_D	-150 [d]	A
	T_C = 70 °C		-150 [d]	
Pulsed drain current (100 µs)		I_{DM}	-250	
Avalanche current	L = 0.1 mH	I_{AS}	-75	
Single pulse avalanche energy [a]		E_{AS}	281	mJ
Power dissipation	T_C = 25 °C [c]	P_D	375	W
	T_C = 125 °C [b]		125	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [b]	R_{thJA}	40	°C/W
Junction-to-case		R_{thJC}	0.4	

Notes

a. Duty cycle ≤ 1 %
b. When mounted on 1" square PCB (FR4 material)
c. See SOA curve for voltage derating
d. Limited by package

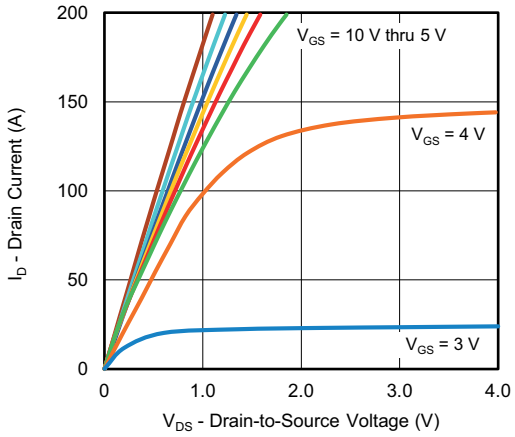
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -10 mA	-80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1.5	-	-2.5	
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -80 V, V_{GS} = 0 V	-	-	-1	µA
		V_{DS} = -80 V, V_{GS} = 0 V, T_J = 125 °C	-	-	-50	
		V_{DS} = -80 V, V_{GS} = 0 V, T_J = 175 °C	-	-	-250	
On-state drain current [a]	$I_{D(on)}$	$V_{DS} \leq$ -5 V, V_{GS} = -10 V	-30	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -20 A	-	0.0048	0.0058	Ω
		V_{GS} = -4.5 V, I_D = -15 A	-	0.0065	0.0081	
Forward transconductance [a]	g_{fs}	V_{DS} = -15 V, I_D = -15 A	-	80	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = -40 V, f = 1 MHz	-	9600	-	pF
Output capacitance	C_{oss}		-	3300	-	
Reverse transfer capacitance	C_{rss}		-	110	-	
Total gate charge [c]	Q_g	V_{DS} = -40 V, V_{GS} = -10 V, I_D = -110 A	-	145	218	nC
Gate-source charge [c]	Q_{gs}		-	34	-	
Gate-drain charge [c]	Q_{gd}		-	16	-	
Gate resistance	R_g	f = 1 MHz	0.46	2.3	4.6	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = -40 V, R_L = 0.71 Ω $I_D \cong$ -20 A, V_{GEN} = -10 V, R_g = 1 Ω	-	25	35	ns
Rise time [c]	t_r		-	20	30	
Turn-off delay time [c]	$t_{d(off)}$		-	90	140	
Fall time [c]	t_f		-	20	30	
Drain-Source Body Diode Characteristics (T_C = 25 °C [b])						
Continuous current	I_S		-	-	-150	A
Pulsed current	I_{SM}		-	-	-250	
Forward voltage [a]	V_{SD}	I_F = -10 A, V_{GS} = 0 V	-	-0.8	-1.5	V
Reverse recovery time	t_{rr}	I_F = -20 A, dI/dt = 100 A/µs	-	90	135	ns
Peak reverse recovery charge	$I_{RM(REC)}$		-	-2.8	-4.2	A
Reverse recovery charge	Q_{rr}		-	145	218	nC

Notes

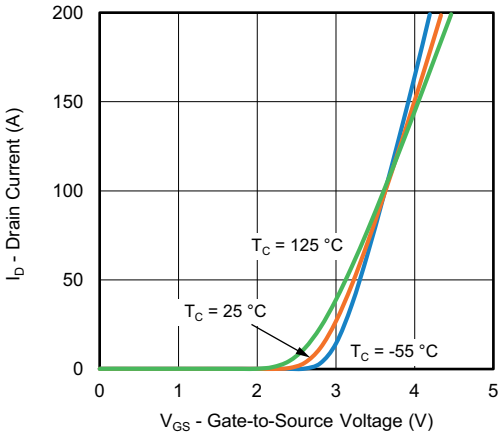
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

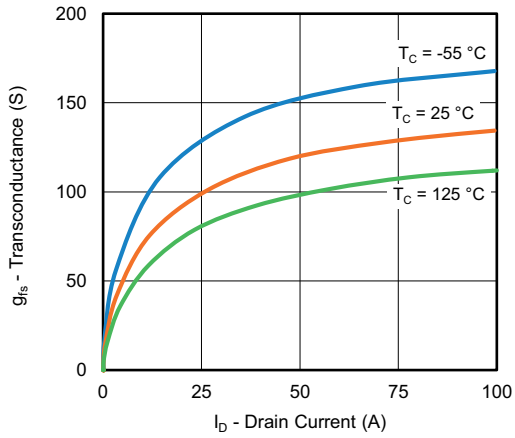
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



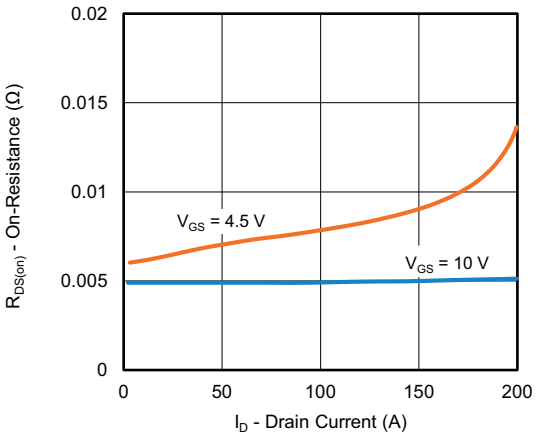
Output Characteristics



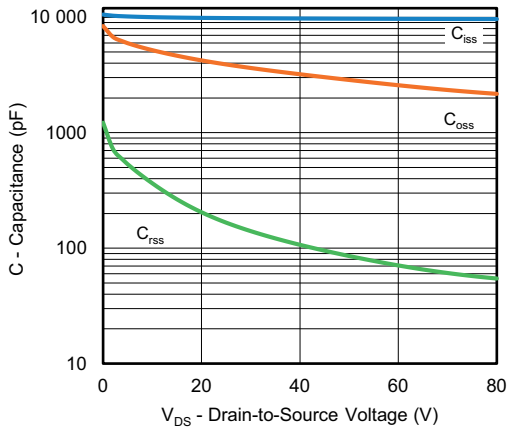
Transfer Characteristics



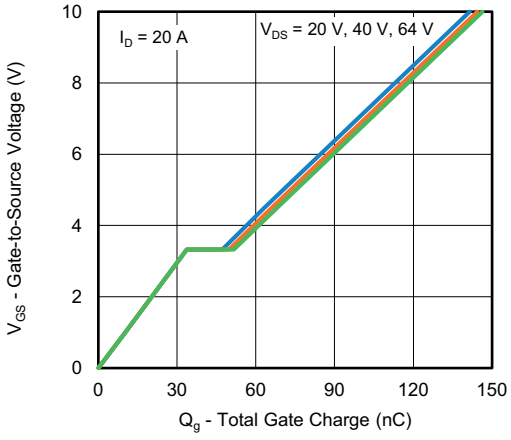
Transconductance



On-Resistance vs. Drain Current

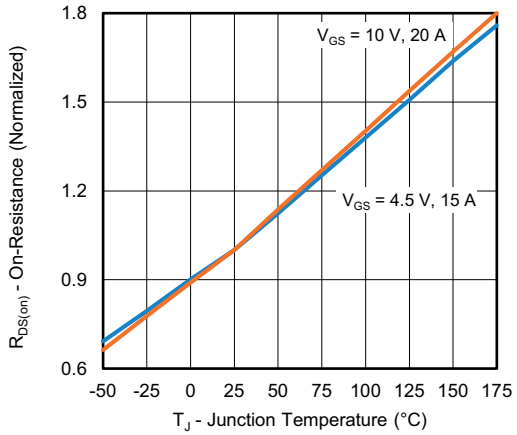


Capacitance

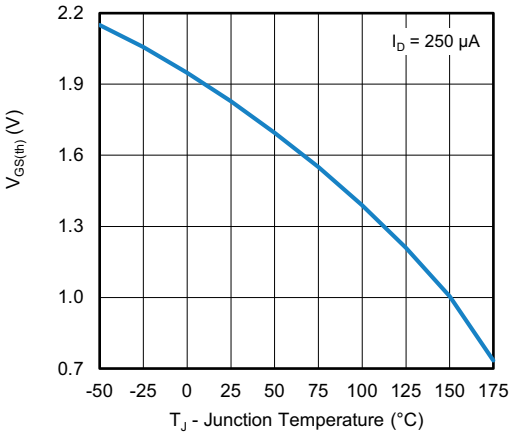


Gate Charge

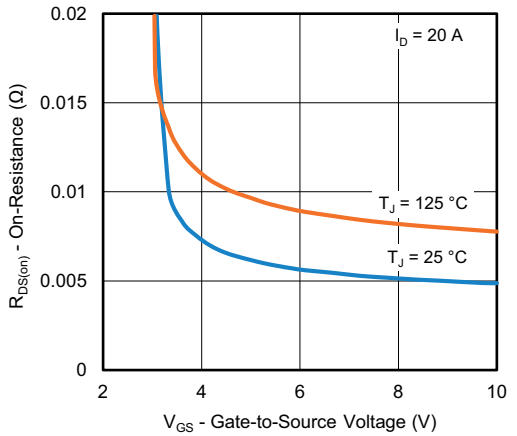
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



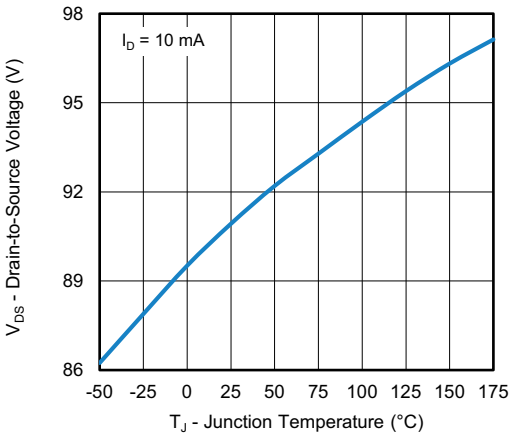
On-Resistance vs. Junction Temperature



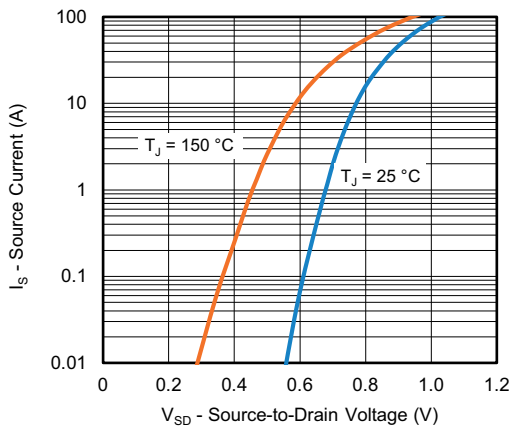
Threshold Voltage



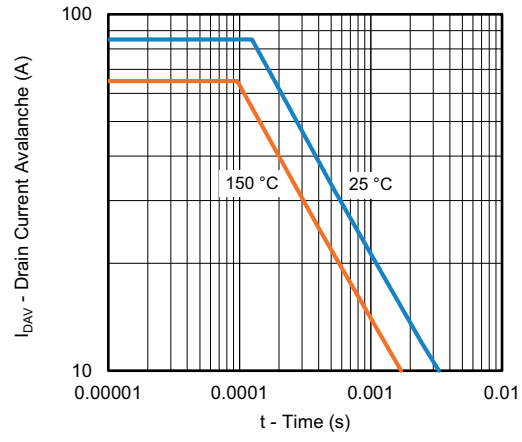
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

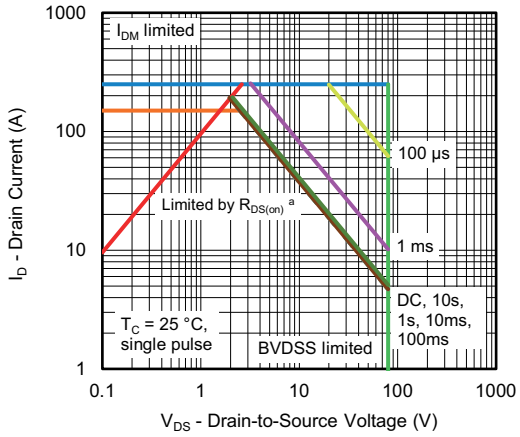


Source Drain Diode Forward Voltage



Avalanche Current vs. Time

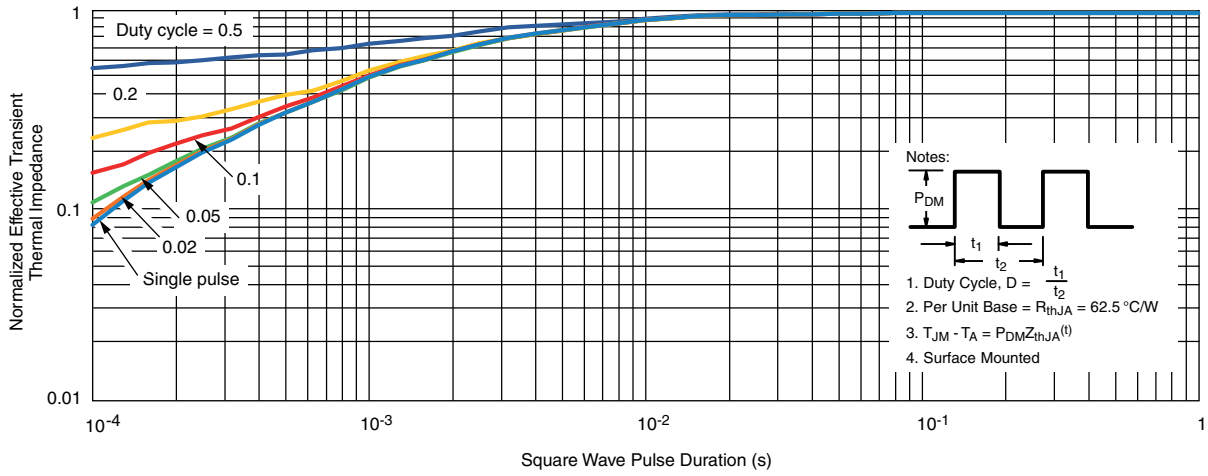
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63020.

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.